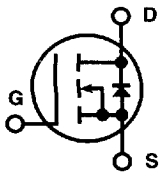

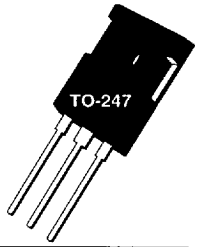

ADVANCED POWER TECHNOLOGY®

APT1001RBNR 1000V 11.0A 1.00Ω
APT1001R1BNR 1000V 10.5A 1.10Ω

POWER MOS IV® **AVALANCHE RATED**

N-CHANNEL ENHANCEMENT MODE HIGH VOLTAGE POWER MOSFETS

MAXIMUM RATINGS All Ratings: $T_C = 25°C$ unless otherwise specified.

Symbol	Parameter	APT1001RBNR	APT1001R1BNR	UNIT
V_{DSS}	Drain-Source Voltage	1000	1000	Volts
I_D	Continuous Drain Current @ $T_C = 25°C$	11	10.5	Amps
I_{DM}	Pulsed Drain Current ①	44	42	
V_{GS}	Gate-Source Voltage Continuous	±20		Volts
V_{GSM}	Gate-Source Voltage Transient	±30		
P_D	Total Power Dissipation @ $T_C = 25°C$	310		Watts
	Linear Derating Factor	2.5		W/°C
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150		°C
T_L	Lead Temperature: 0.063" from Case for 10 Sec.	300		
I_{AR}	Avalanche Current ① (Repetitive and Non-Repetitive)	11		Amps
E_{AR}	Repetitive Avalanche Energy ①	25		mJ
E_{AS}	Single Pulse Avalanche Energy ④	1210		

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions / Part Number		MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage ($V_{GS} = 0V$, $I_D = 250\ \mu A$)		1000			Volts
$I_{D(ON)}$	On State Drain Current ②	APT1001RBNR	11			Amps
	($V_{DS} > I_{D(ON)} \times R_{DS(ON)}$ Max, $V_{GS} = 10V$)	APT1001R1BNR	10.5			
$R_{DS(ON)}$	Drain-Source On-State Resistance ②	APT1001RBNR			1.00	Ohms
	($V_{GS} = 10V$, 0.5 I_D [Cont.])	APT1001R1BNR			1.10	
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = V_{DSS}$, $V_{GS} = 0V$)				250	µA
	Zero Gate Voltage Drain Current ($V_{DS} = 0.8\ V_{DSS}$, $V_{GS} = 0V$, $T_C = 125°C$)				1000	
I_{GSS}	Gate-Source Leakage Current ($V_{GS} = \pm 20V$, $V_{DS} = 0V$)				±100	nA
$V_{GS(TH)}$	Gate Threshold Voltage ($V_{DS} = V_{GS}$, $I_D = 1.0mA$)		2		4	Volts

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.40	°C/W
$R_{\theta JA}$	Junction to Ambient			40	

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

USA
405 S.W. Columbia Street Bend, Oregon 97702-1035 Phone: (503) 382-8028 FAX: (503) 388-0364
EUROPE
Avenue J.F. Kennedy Bât B4 Parc Cadéra Nord F-33700 Merignac - France Phone: (33) 56 34 34 71 FAX: (33) 56 47 97 61

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DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1 MHz		3400	4000	pF
C_{oss}	Output Capacitance			330	500	
C_{rss}	Reverse Transfer Capacitance			126	190	
Q_g	Total Gate Charge ③	V_{GS} = 10V V_{DD} = 0.5 V_{DSS} I_D = I_D [Cont.] @ 25°C		150	210	nC
Q_{gs}	Gate-Source Charge			16	25	
Q_{gd}	Gate-Drain ("Miller") Charge			75	110	
$t_d(on)$	Turn-on Delay Time	V_{GS} = 15V V_{DD} = 0.5 V_{DSS} I_D = I_D [Cont.] @ 25°C R_G = 1.8Ω		18	36	ns
t_r	Rise Time			22	45	
$t_d(off)$	Turn-off Delay Time			110	160	
t_f	Fall Time			42	85	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions / Part Number		MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode)	APT1001RBNR			11	Amps
		APT1001R1BNR			10.5	
I_{SM}	Pulsed Source Current ① (Body Diode)	APT1001RBNR			44	
		APT1001R1BNR			42	
V_{SD}	Diode Forward Voltage ② (V_{GS} = 0V, I_S = -I_D [Cont.])				1.3	Volts
t_{rr}	Reverse Recovery Time (I_S = -I_D [Cont.], dI_S/dt = 100A/µs)		250	500	1000	ns
Q_{rr}	Reverse Recovery Charge (I_S = -I_D [Cont.], dI_S/dt = 100A/µs)		2.5	5	10	µC

SAFE OPERATING AREA CHARACTERISTICS

Symbol	Characteristic	Test Conditions / Part Number		MIN	TYP	MAX	UNIT
SOA1	Safe Operating Area	V_{DS} = 0.4 V_{DSS}, I_{DS} = P_D / 0.4 V_{DSS}, t = 1 Sec.		310			Watts
SOA2	Safe Operating Area	I_{DS} = I_D [Cont.], V_{DS} = P_D / I_D [Cont.], t = 1 Sec.		310			
I_{LM}	Inductive Current Clamped		APT1001RBNR	44			Amps
			APT1001R1BNR	42			

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② Pulse Test: Pulse width < 380 µS, Duty Cycle < 2%

③ See MIL-STD-750 Method 3471

④ Starting T_j = +25°C, L = 20mH, R_G = 25Ω, Peak I_L = 11A

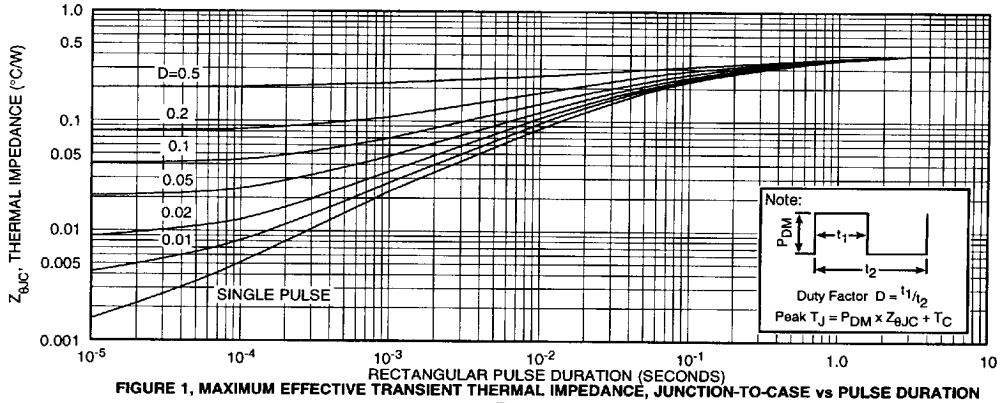


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

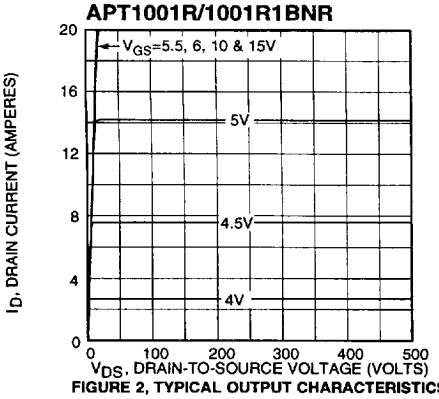


FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS

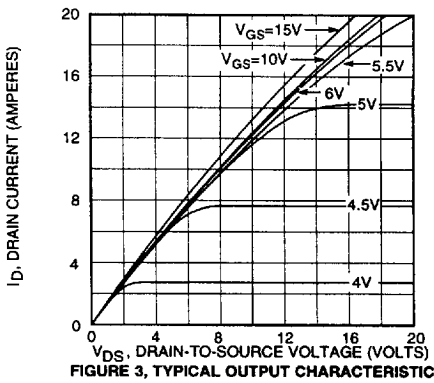


FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS

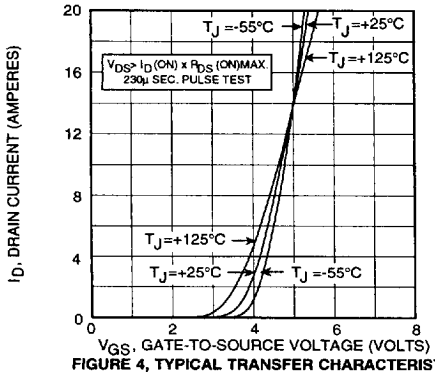


FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS

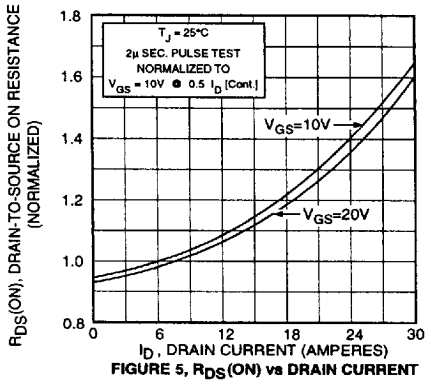


FIGURE 5, R_{DS}(ON) vs DRAIN CURRENT

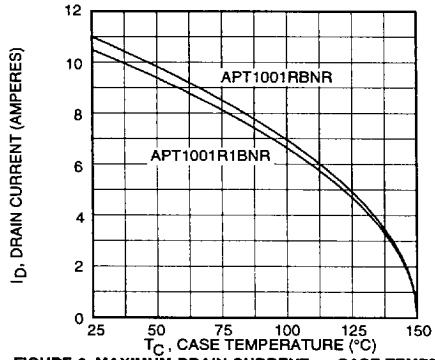


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

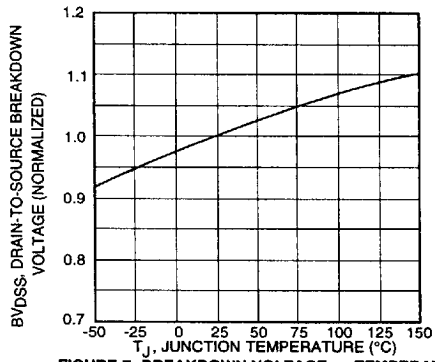


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

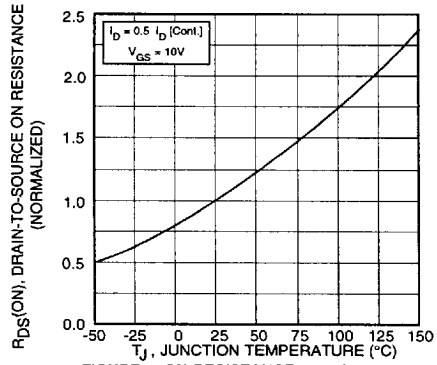


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

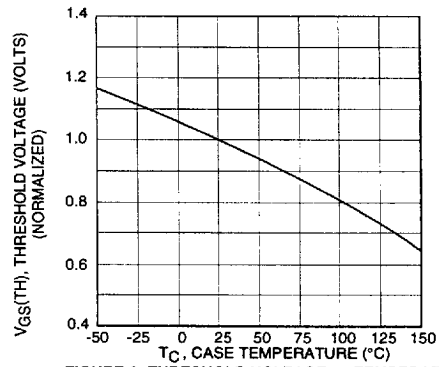


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

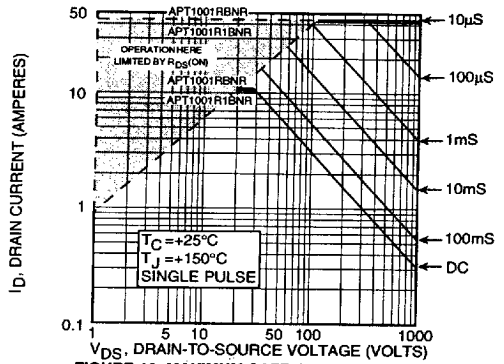


FIGURE 10, MAXIMUM SAFE OPERATING AREA

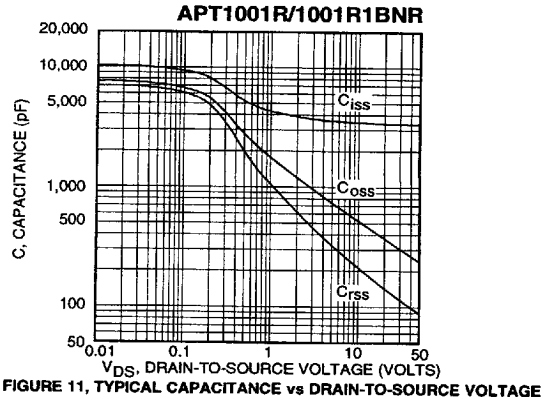


FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

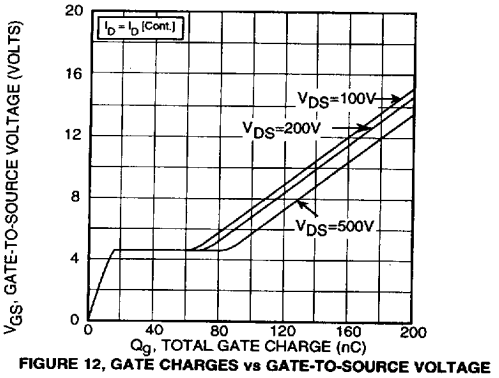


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

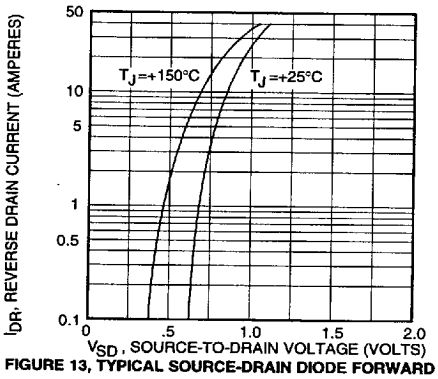
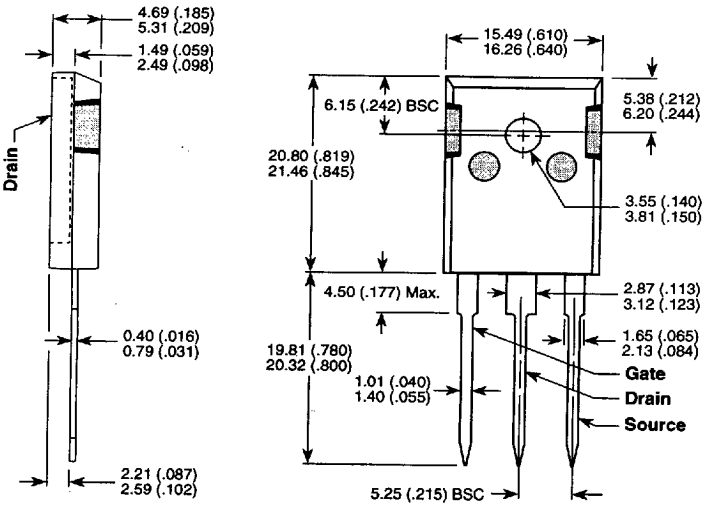


FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE

TO-247AD Package Outline



Dimensions in Millimeters and (Inches)

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